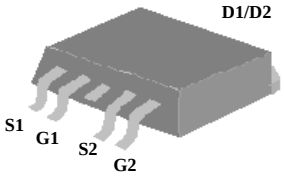
AP4563GH-HF

Halogen-Free Product

Advanced Power Electronics Corp.

N AND P-CHANNEL ENHANCEMENT MODE POWER MOSFET

- ▼ Simple Drive Requirement
- ▼ Good Thermal Performance
- ▼ Fast Switching Performance
- ▼ RoHS Compliant

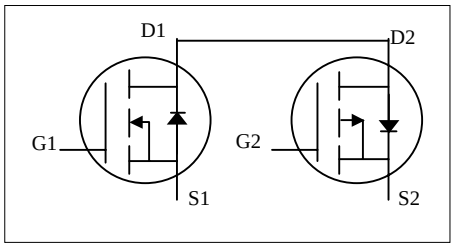


TO-252-4L

N-CH	BV_{DSS}	40V
	$R_{DS(ON)}$	30mΩ
	I_D	8A
P-CH	BV_{DSS}	-40V
	$R_{DS(ON)}$	36mΩ
	I_D	-7.3A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.



Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating		Units
		N-channel	P-channel	
V_{DS}	Drain-Source Voltage	40	-40	V
V_{GS}	Gate-Source Voltage	±20	±20	V
I_D@T_C=25℃	Drain Current , V_{GS} @ 10V	30	-27	A
I_D@T_A=25℃	Drain Current[3] , V_{GS} @ 10V	8.0	-7.3	A
I_D@T_A=70℃	Drain Current[3] , V_{GS} @ 10V	6.3	-5.9	A
I_{DM}	Pulsed Drain Current[1]	40	-40	A
P_D@T_A=25℃	Total Power Dissipation	3.13		W
	Linear Derating Factor	0.025		W/℃
T_{STG}	Storage Temperature Range	-55 to 150		℃
T_J	Operating Junction Temperature Range	-55 to 150		℃

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c (N-CH)	Maximum Thermal Resistance, Junction-case[3]	3.2	℃/W
Rthj-c (P-CH)	Maximum Thermal Resistance, Junction-case[3]	3	℃/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient[3]	40	℃/W

N-CH Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	40	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=8A	-	-	30	mΩ
		V_{GS}=4.5V, I_D=5A	-	-	40	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	1	-	3	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=8A	-	18	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=32V, V_{GS}=0V	-	-	10	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Q_g	Total Gate Charge[2]	I_D=8A	-	13	20.8	nC
Q_{gs}	Gate-Source Charge	V_{DS}=32V	-	3	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=4.5V	-	8	-	nC
$t_{d(on)}$	Turn-on Delay Time[2]	V_{DS}=20V	-	8	-	ns
t_r	Rise Time	I_D=1A	-	5.5	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω	-	23	-	ns
t_f	Fall Time	V_{GS}=10V	-	6	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	960	1760	pF
C_{oss}	Output Capacitance	V_{DS}=25V	-	105	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	90	-	pF
R_g	Gate Resistance	f=1.0MHz	-	1.5	2.7	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=2.4A, V_{GS}=0V	-	-	1.3	V
t_{rr}	Reverse Recovery Time[2]	I_S=8A, V_{GS}=0V	-	20	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	14	-	nC

P-CH Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250uA	-40	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V, I_D=-7A	-	-	36	mΩ
		V_{GS}=-4.5V, I_D=-5A	-	-	48	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250uA	-1	-	-3	V
g_{fs}	Forward Transconductance	V_{DS}=-10V, I_D=-7A	-	19	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-32V, V_{GS}=0V	-	-	-10	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Q_g	Total Gate Charge[2]	I_D=-7A	-	18	30	nC
Q_{gs}	Gate-Source Charge	V_{DS}=-32V	-	3	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=-4.5V	-	10	-	nC
$t_{d(on)}$	Turn-on Delay Time[2]	V_{DS}=-20V	-	10	-	ns
t_r	Rise Time	I_D=-1A	-	5	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω	-	46	-	ns
t_f	Fall Time	V_{GS}=-10V	-	30	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	1360	2500	pF
C_{oss}	Output Capacitance	V_{DS}=-25V	-	155	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	140	-	pF
R_g	Gate Resistance	f=1.0MHz	-	7	13	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=-2.4A, V_{GS}=0V	-	-	-1.3	V
t_{rr}	Reverse Recovery Time[2]	I_S=-7A, V_{GS}=0V	-	23	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=-100A/μs	-	16	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.N-CH , P-CH are same.

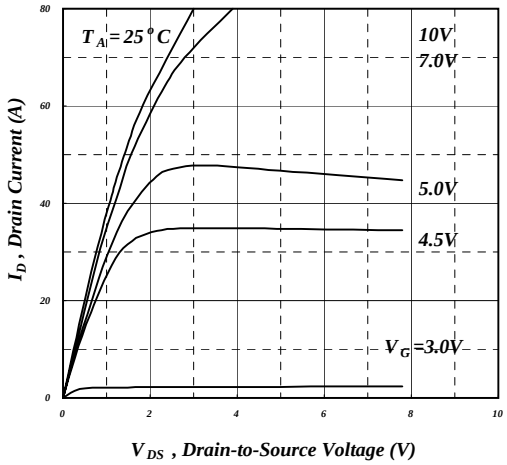


Fig 1. Typical Output Characteristics

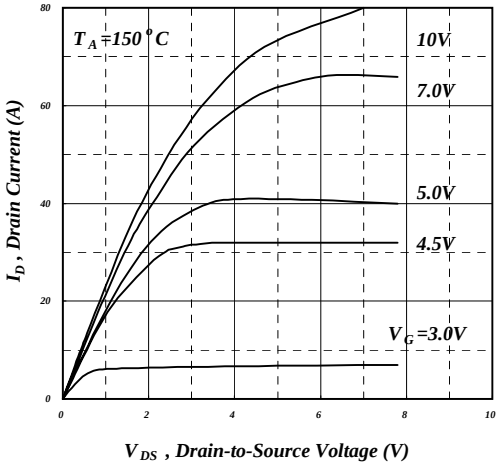


Fig 2. Typical Output Characteristics

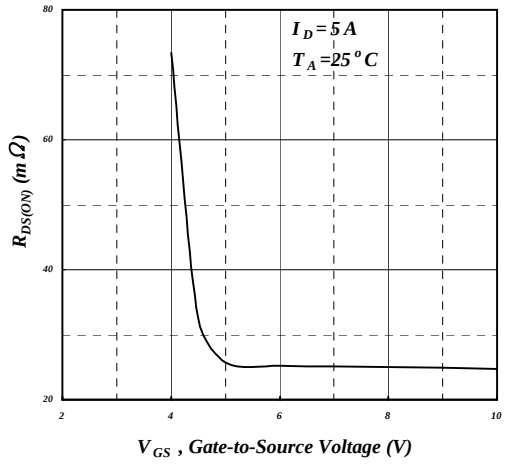


Fig 3. On-Resistance v.s. Gate Voltage

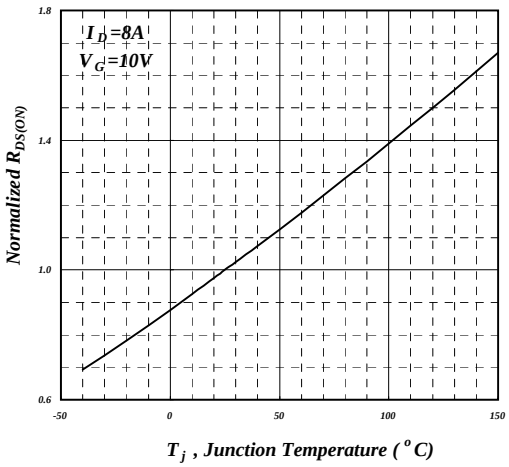


Fig 4. Normalized On-Resistance v.s. Junction Temperature

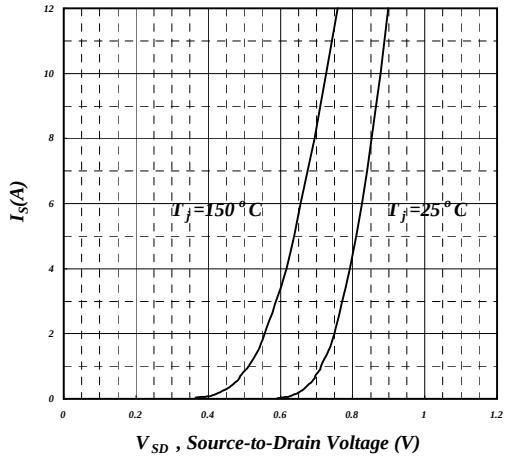


Fig 5. Forward Characteristic of Reverse Diode

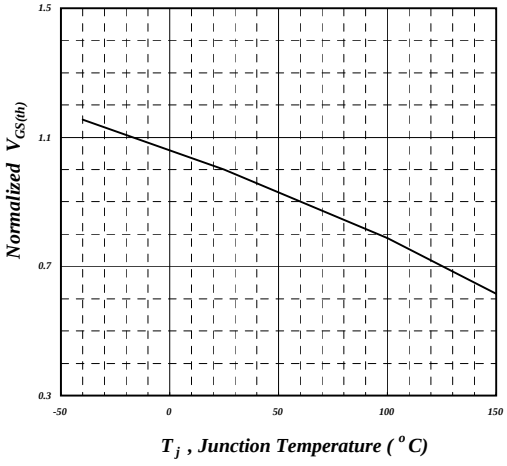


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

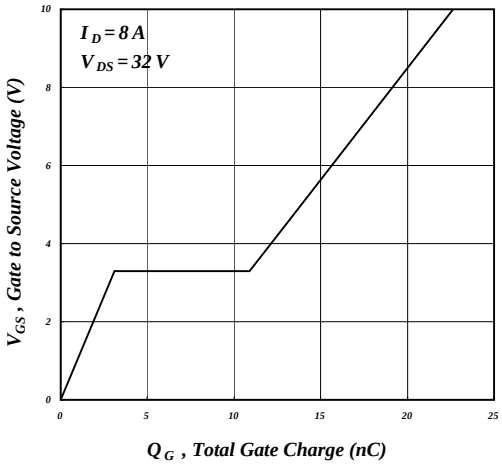


Fig 7. Gate Charge Characteristics

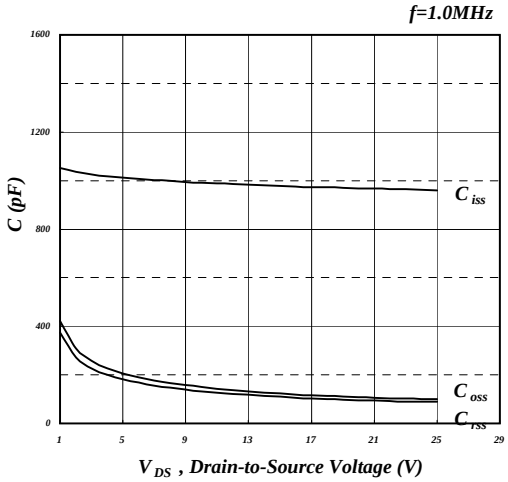


Fig 8. Typical Capacitance Characteristics

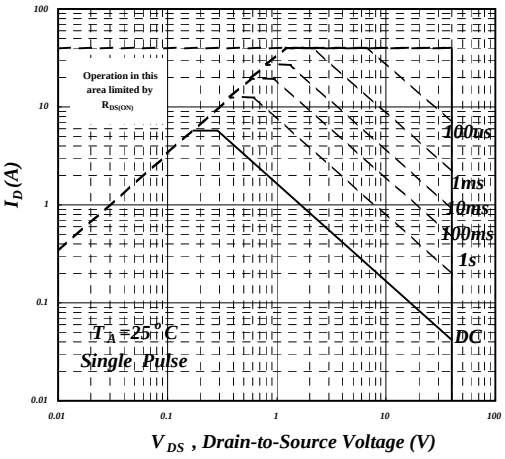


Fig 9. Maximum Safe Operating Area

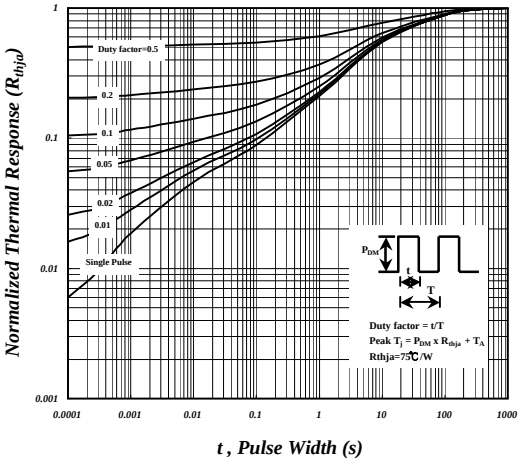


Fig 10. Effective Transient Thermal Impedance

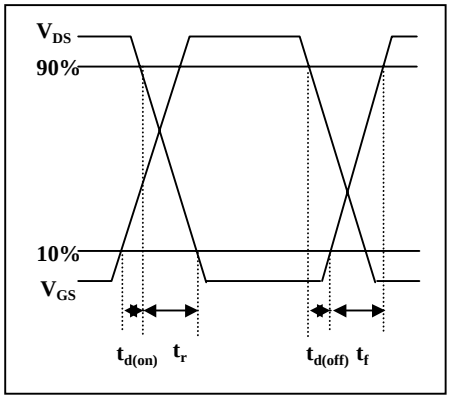


Fig 11. Switching Time Waveform

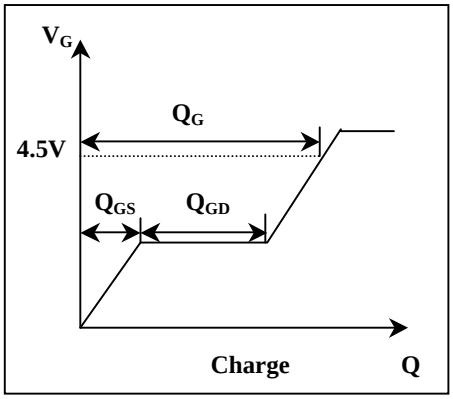


Fig 12. Gate Charge Waveform

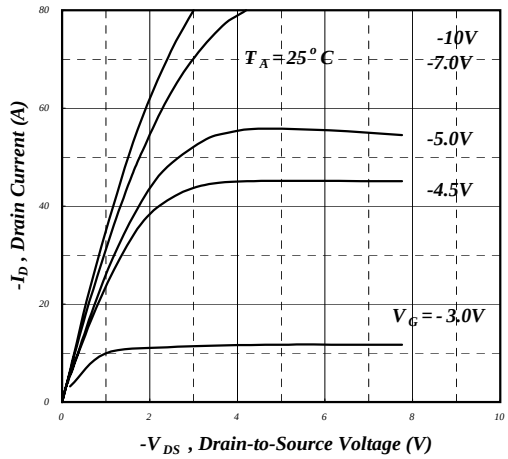


Fig 1. Typical Output Characteristics

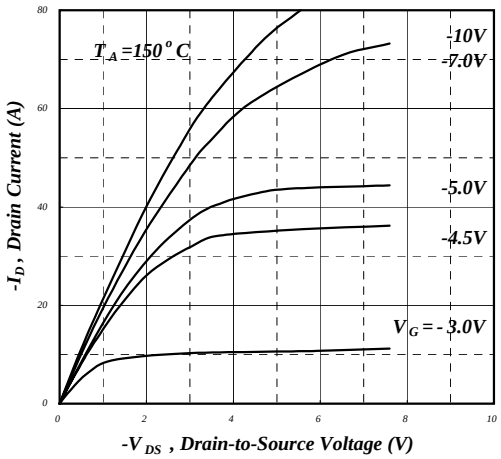


Fig 2. Typical Output Characteristics

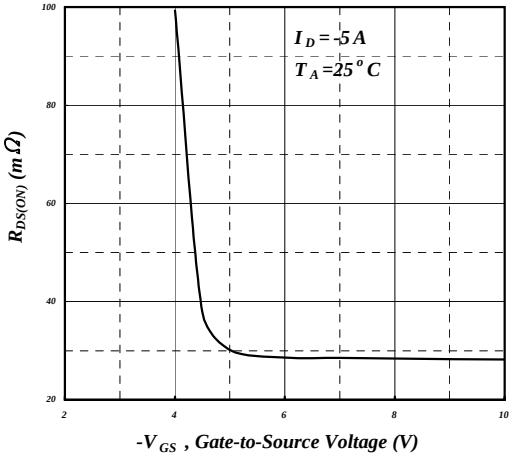


Fig 3. On-Resistance v.s. Gate Voltage

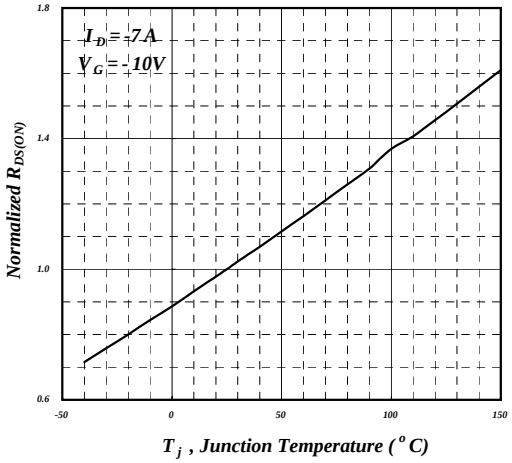


Fig 4. Normalized On-Resistance v.s. Junction Temperature

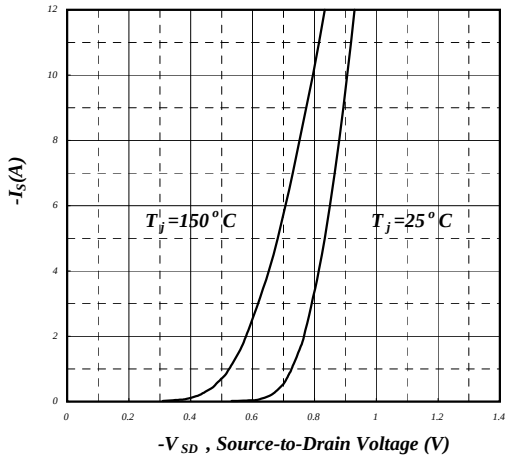


Fig 5. Forward Characteristic of Reverse Diode

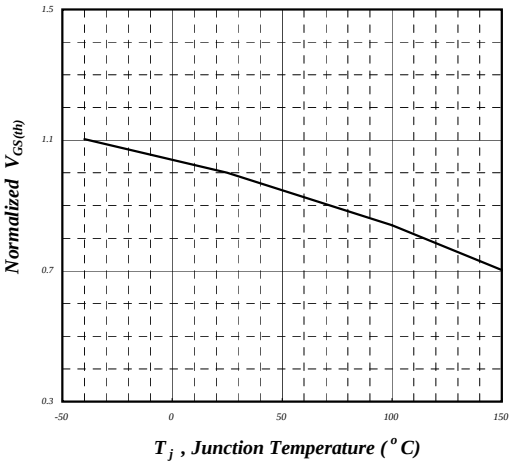


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

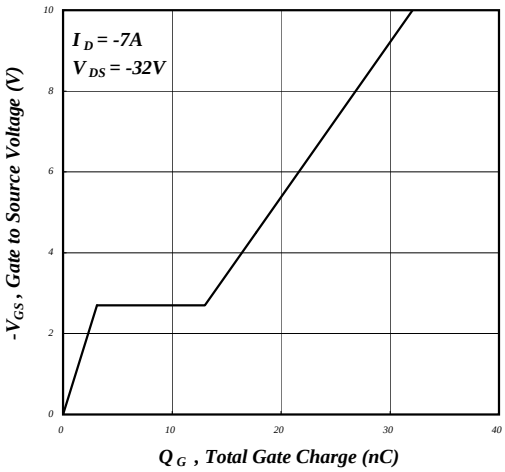
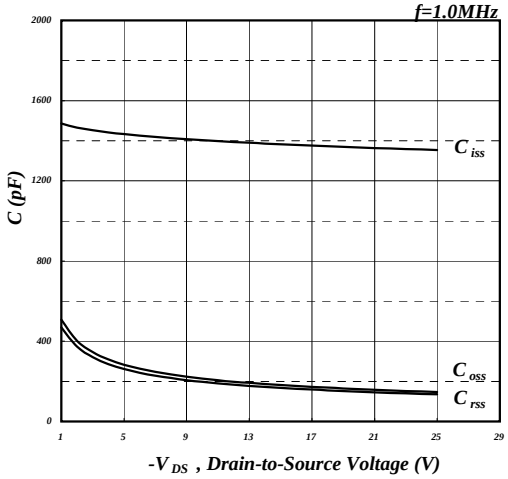


Fig 7. Gate Charge Characteristics



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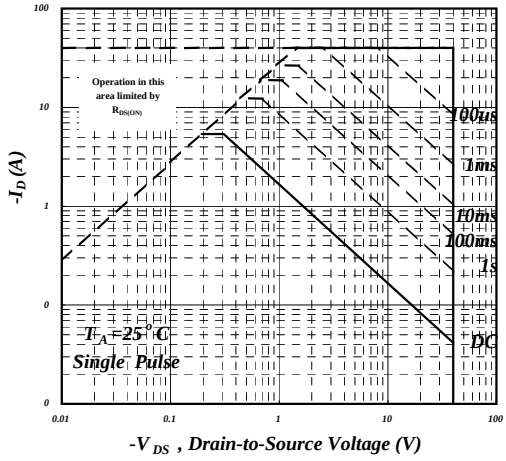

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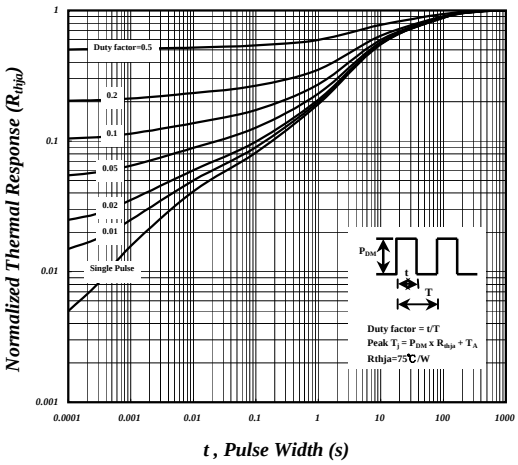
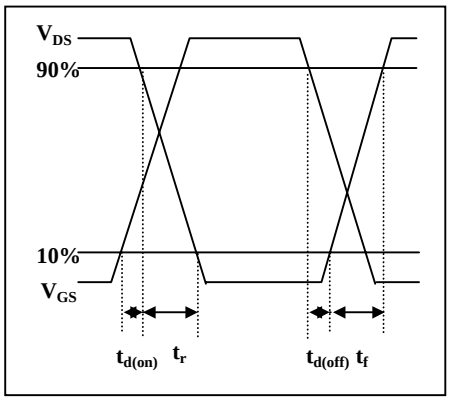


Fig 10. Effective Transient Thermal Impedance



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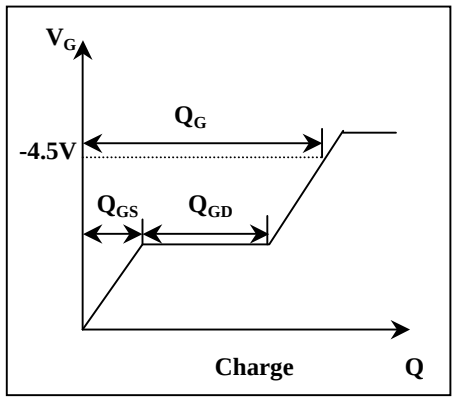
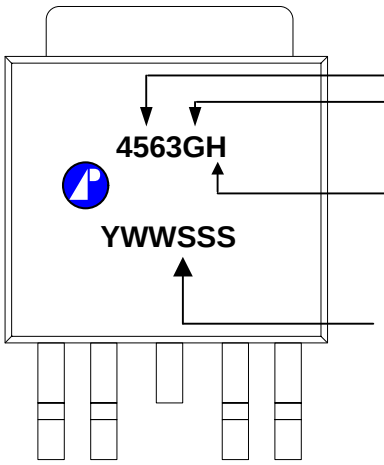


Fig 12. Gate Charge Waveform

MARKING INFORMATION



Part Number
meet Rohs requirement
for low voltage MOSFET only
Package Code
Date Code (YWWSSS)
Y：Last Digit Of The Year
WW：Week
SSS：Sequence